

Application Data Sheet

Application Information

Application Type::	Regular
Subject Matter::	Utility
Suggested Group Art Unit::	N/A
CD-ROM or CD-R?::	None
Sequence submission?::	None
Computer Readable Form (CRF)?::	No
Title::	ATOMIC LAYER DEPOSITION OF TITANIUM NITRIDE USING BATCH TYPE CHAMBER AND METHOD FOR FABRICATING CAPACITOR BY USING THE SAME
Attorney Docket Number::	29926/39505
Request for Early Publication?::	No
Request for Non-Publication?::	No
Total Drawing Sheets::	10
Small Entity?::	No
Petition included?::	No
Secrecy Order in Parent Appl.?::	No

Applicant Information

Applicant Authority Type::	Inventor
Primary Citizenship Country::	Korea, Republic of
Status::	Full Capacity
Given Name::	Young-Soo
Family Name::	Kim
City of Residence::	Kyoungki-do
Country of Residence::	Korea
Street of mailing address::	San 136-1, ami-Ri Bubal-Eub Ichon-shi,



City of mailing address:: Kyoungki-do
Country of mailing address:: Korea, Republic of
Postal or Zip Code of mailing address:: 467-860

Correspondence Information

Correspondence Customer Number:: 04743

Representative Information

Representative Customer Number:: 04743

Foreign Priority Information

Country::	Application number::	FilingDate::	Priority Claimed::
Korea, Republic of	2002-42296	07/19/02	Yes

Assignee Information

Assignee name:: HYNIX SEMICONDUCTOR INC.
Street of mailing address:: San 136-1, Ami-Ri, Bubal-Eub, Ichon-Shi
City of mailing address:: Kyoungki-Do
Country of mailing address:: Korea, Republic of
Postal or Zip Code of mailing address:: 467-860